

<IGBT Modules>

CM100DY-13T

HIGH POWER SWITCHING USE
INSULATED TYPE



dual switch (half-bridge)

Collector current I_C **1 0 0 A**
 Collector-emitter voltage V_{CES} **6 5 0 V**
 Maximum junction temperature T_{vjmax} **1 7 5 °C**

- dual switch (half-bridge)
- Nickel-plating tab terminals
- RoHS Directive compliant
- UL Recognized under UL1557, File No. E323585

APPLICATION

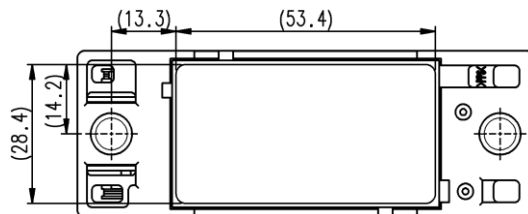
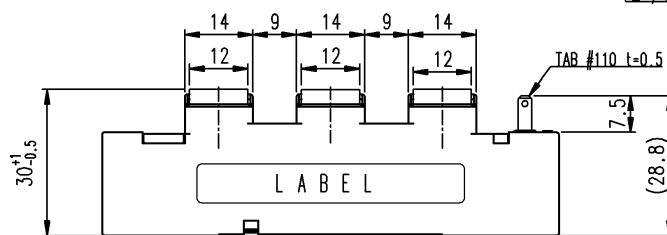
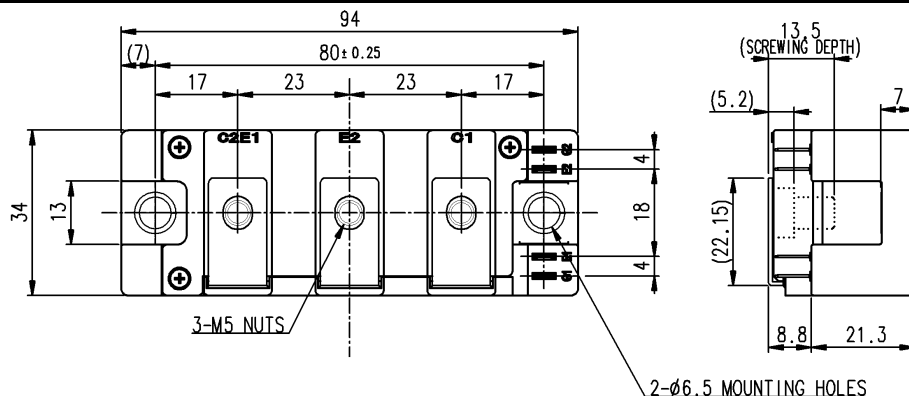
AC Motor Control, Motion/Servo Control, Power supply, etc.

OPTION (Below options are available.)

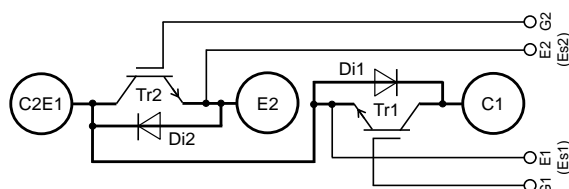
- PC-TIM (Phase Change Thermal Interface Material) pre-apply (Note8)

OUTLINE DRAWING & INTERNAL CONNECTION

Dimension in mm



INTERNAL CONNECTION



Tolerance otherwise specified		
Division of Dimension		Tolerance
0.5	to 3	±0.2
over 3	to 6	±0.3
over 6	to 30	±0.5
over 30	to 120	±0.8
over 120	to 400	±1.2

JIS B 0405 c

CM100DY-13T

HIGH POWER SWITCHING USE
INSULATED TYPEMAXIMUM RATINGS (T_{vj}=25 °C, unless otherwise specified)

Symbol	Item	Conditions	Rating	Unit
V _{CES}	Collector-emitter voltage	G-E short-circuited	650	V
V _{GES}	Gate-emitter voltage	C-E short-circuited	± 20	V
I _C	Collector current	DC, T _C =143 °C* (Note2, 4)	100	A
I _{CRM}		Pulse, Repetitive (Note3)	200	
P _{tot}	Total power dissipation	T _C =25 °C (Note2, 4)	775	W
I _E (Note1)	Emitter current	DC (Note2)	100	A
I _{ERM} (Note1)		Pulse, Repetitive (Note3)	200	
V _{isol}	Isolation voltage	Terminals to base plate, RMS, f=60 Hz, AC 1 min	4000	V
T _{vjmax}	Maximum junction temperature	Instantaneous event (overload) (Note8)	175	°C
T _{Cmax}	Maximum case temperature	(Note4,8)	150*	
T _{vjop}	Operating junction temperature	Continuous operation (under switching) (Note8)	-40 ~ +150	°C
T _{stg}	Storage temperature	-	-40 ~ +150*	

ELECTRICAL CHARACTERISTICS (T_{vj}=25 °C, unless otherwise specified)

Symbol	Item	Conditions	Limits			Unit
			Min.	Typ.	Max.	
I _{CES}	Collector-emitter cut-off current	V _{CE} =V _{CES} , G-E short-circuited	-	-	1.0	mA
I _{GES}	Gate-emitter leakage current	V _{GE} =V _{GES} , C-E short-circuited	-	-	0.5	μA
V _{GE(th)}	Gate-emitter threshold voltage	I _C =10 mA, V _{CE} =10 V	5.4	6.0	6.6	V
V _{CESat} (Terminal)	Collector-emitter saturation voltage	I _C =100 A, V _{GE} =15 V, Refer to the figure of test circuit (Note5)	T _{vj} =25 °C	1.35	1.65	V
			T _{vj} =125 °C	1.45	-	
			T _{vj} =150 °C	1.50	-	
V _{CESat} (Chip)		I _C =100 A, V _{GE} =15 V, (Note5)	T _{vj} =25 °C	1.30	1.55	V
			T _{vj} =125 °C	1.35	-	
			T _{vj} =150 °C	1.35	-	
C _{ies}	Input capacitance	V _{CE} =10 V, G-E short-circuited	-	-	13.4	nF
C _{oes}	Output capacitance		-	-	0.6	
C _{res}	Reverse transfer capacitance		-	-	0.3	
Q _G	Gate charge	V _{CC} =300 V, I _C =100 A, V _{GE} =15 V	-	0.41	-	μC
t _{d(on)}	Turn-on delay time	V _{CC} =300 V, I _C =100 A, V _{GE} =±15 V, R _G =6.2 Ω, Inductive load	-	-	200	ns
t _r	Rise time		-	-	150	
t _{d(off)}	Turn-off delay time		-	-	400	
t _f	Fall time		-	-	400	
V _{EC} (Note.1) (Terminal)	Emitter-collector voltage	I _E =100 A, G-E short-circuited, Refer to the figure of test circuit (Note5)	T _{vj} =25 °C	2.05	2.85	V
			T _{vj} =125 °C	1.95	-	
			T _{vj} =150 °C	1.95	-	
V _{EC} (Note.1) (Chip)		I _E =100 A, G-E short-circuited, (Note5)	T _{vj} =25 °C	1.90	2.65	V
			T _{vj} =125 °C	1.80	-	
			T _{vj} =150 °C	1.80	-	
t _{rr} (Note1)	Reverse recovery time	V _{CC} =300 V, I _E =100 A, V _{GE} =±15 V, R _G =6.2 Ω, Inductive load	-	-	150	ns
Q _{rr} (Note1)	Reverse recovery charge		-	3.5	-	μC
E _{on}	Turn-on switching energy per pulse	V _{CC} =300 V, I _C =I _E =100 A,	-	1.2	-	mJ
E _{off}	Turn-off switching energy per pulse	V _{GE} =±15 V, R _G =6.2 Ω, T _{vj} =150 °C,	-	5.1	-	
E _{rr} (Note1)	Reverse recovery energy per pulse	Inductive load	-	1.8	-	mJ
R _{CC'+EE'}	Internal lead resistance	Main terminals-chip, per switch, T _C =25 °C (Note4)	-	0.2	-	mΩ
r _g	Internal gate resistance	Per switch	-	0	-	Ω

*: The value of PC-TIM applied module is limited by the heat resistant temperature of PC-TIM.

THERMAL RESISTANCE CHARACTERISTICS

Symbol	Item	Conditions	Limits			Unit
			Min.	Typ.	Max.	
$R_{th(j-c)Q}$	Thermal resistance	Junction to case, per Inverter IGBT (Note4)	-	-	193	K/kW
$R_{th(j-c)D}$		Junction to case, per Inverter FWD (Note4)	-	-	304	
$R_{th(c-s)}$	Contact thermal resistance	Case to heat sink, per 1 module Thermal grease applied (Note4,6,8)	-	36.6	-	K/kW

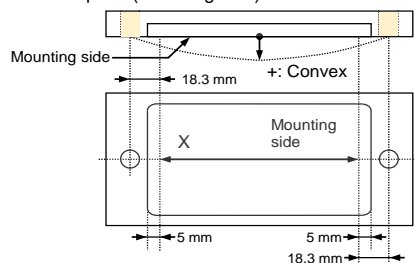
MECHANICAL CHARACTERISTICS

Symbol	Item	Conditions	Limits			Unit
			Min.	Typ.	Max.	
M_t	Mounting torque	Main terminals M 5 screw	2.5	3.0	3.5	N·m
M_s	Mounting torque	Mounting to heat sink M 6 screw	3.5	4.0	4.5	N·m
d_s	Creepage distance	Terminal to terminal	18.4	-	-	mm
		Terminal to base plate	21.1	-	-	
d_a	Clearance	Terminal to terminal	9.6	-	-	mm
		Terminal to base plate	16.7	-	-	
e_c	Flatness of base plate	On the centerline (Note7)	± 0	-	+200	μm
m	mass	-	-	120	-	g

*. This product is compliant with the Restriction of the Use of Certain Hazardous Substances in Electrical and Electronic Equipment (RoHS) directive 2011/65/EU and (EU) 2015/863.

Note1. Represent ratings and characteristics of the anti-parallel, emitter-collector free-wheeling diode (FWD).

- Junction temperature (T_{vj}) should not increase beyond $T_{vj\max}$ rating.
- Pulse width and repetition rate should be such that the device junction temperature (T_{vj}) does not exceed $T_{vj\max}$ rating.
- Case temperature (T_c) and heat sink temperature (T_s) are defined on the each surface (mounting side) of base plate and heat sink just under the chips. Refer to the figure of chip location.
- Pulse width and repetition rate should be such as to cause negligible temperature rise. Refer to the figure of test circuit.
- Typical value is measured by using thermally conductive grease of $\lambda=3.0 \text{ W/(m}\cdot\text{K)}/D_{(C-S)}=50 \mu\text{m}$.
- The base plate (mounting side) flatness measurement point is as follows of the following figure.



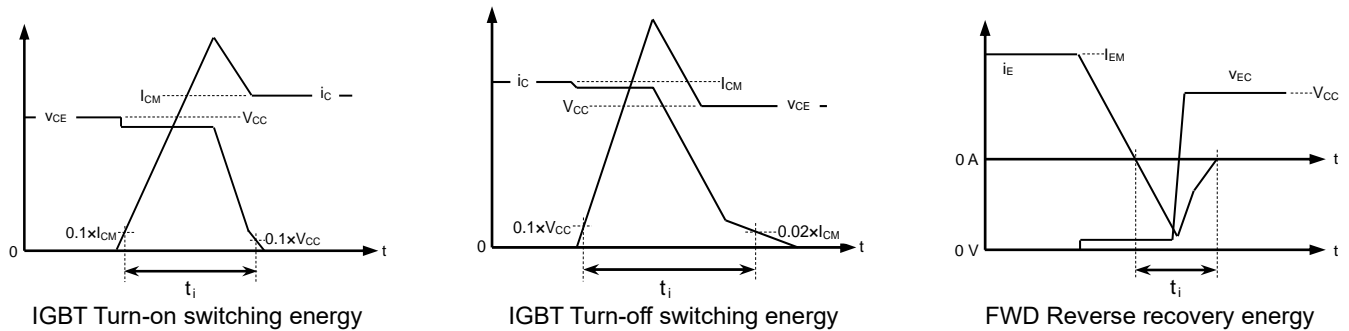
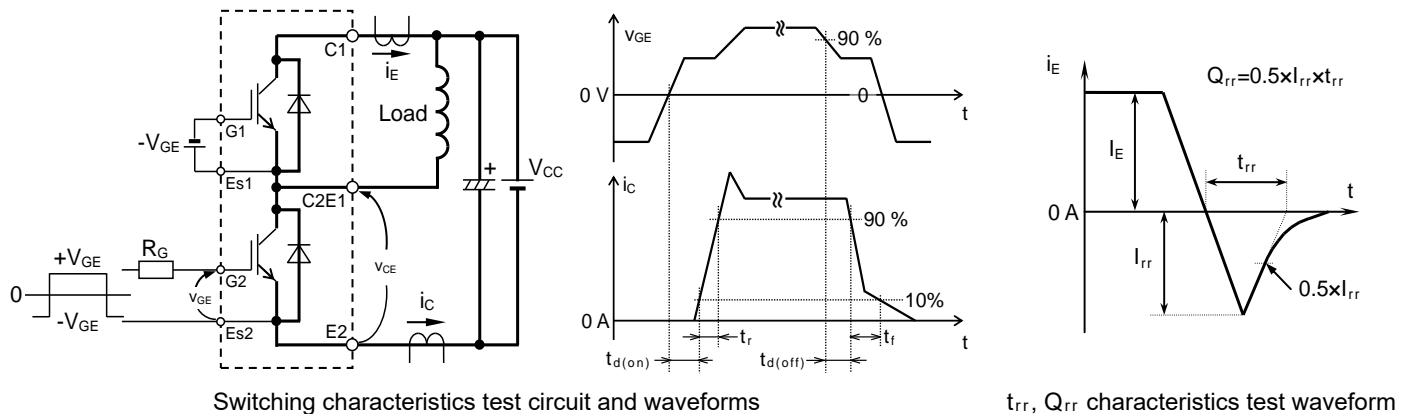
- Long term performance related to thermal conductive grease and PC-TIM (including but not limited to aspects such as the increase of thermal resistance due to pumping out, etc.) should be verified under your specific application conditions. Each temperature condition ($T_{vj\max}$, $T_{vj\text{op}}$, $T_{c\max}$) must be maintained below the maximum rated temperature throughout consideration of the temperature rise even for long term usage.

CHIP LOCATION (Top view)

Technical drawing of the front view of a rectangular component. The overall width is 94 and the overall height is 34. The component features a central section with two circular features labeled Tr 1 and Tr 2, and two rectangular features labeled Di 1 and Di 2. The left side has a circular feature labeled C2E1 and a circular feature labeled Tr 2. The right side has a circular feature labeled C1, a circular feature labeled Tr 1, and a circular feature labeled E2. The bottom edge is labeled 0, 7.0, 29.8, 42.4, 57.3, and 64. The top edge is labeled 0, 18.8 (Tr 2), 18.5 (Di 2), 18.8 (Tr 1), 18.4 (Di 1), and 17.0. The text "LABEL SIDE" is located at the bottom right.

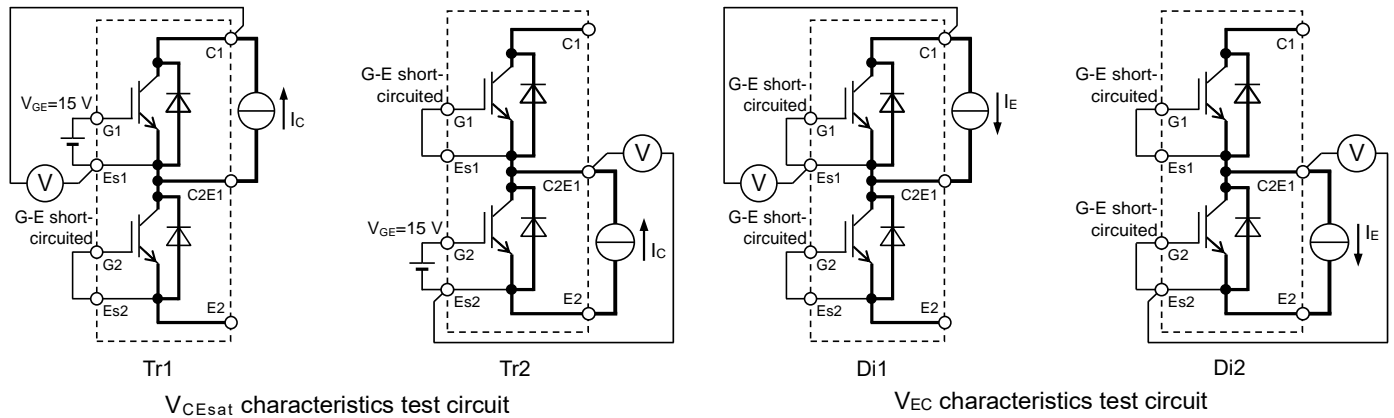
Tr1/Tr2: IGBT, Di1/Di2: FWD

TEST CIRCUIT AND WAVEFORMS



Turn-on / Turn-off switching energy and Reverse recovery energy test waveforms (Integral time instruction drawing)

TEST CIRCUIT

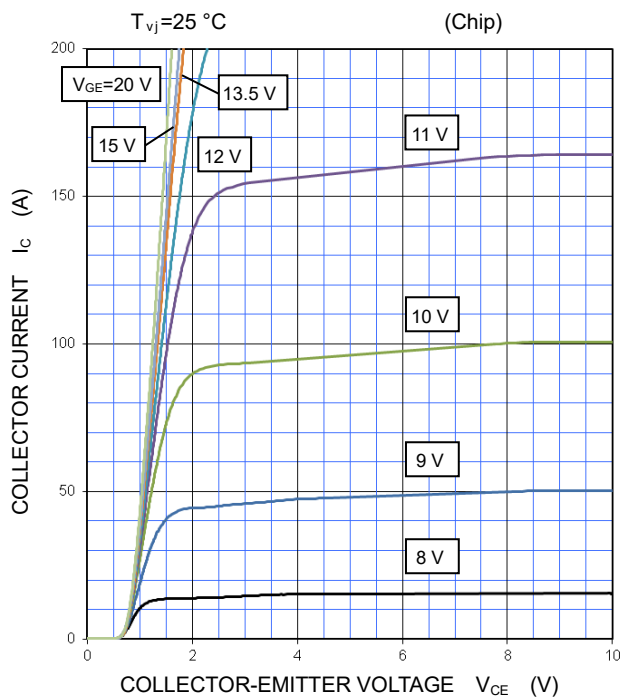


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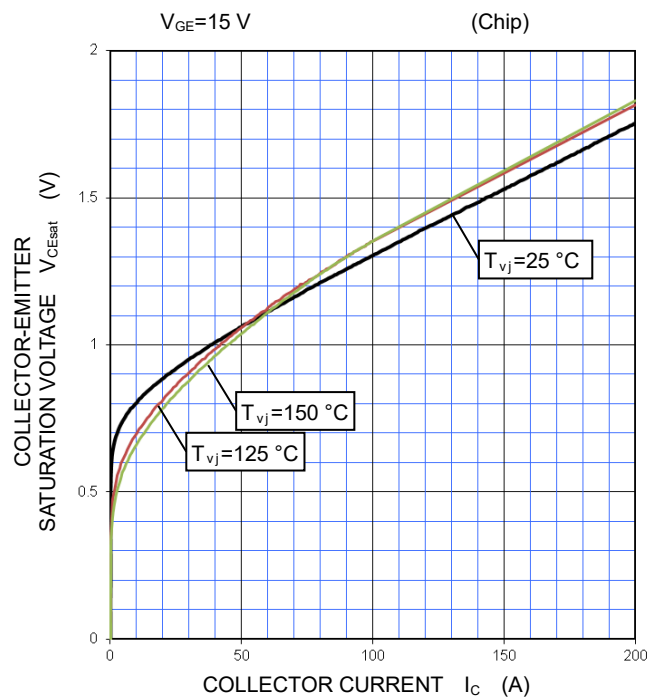
HIGH POWER SWITCHING USE
INSULATED TYPE

PERFORMANCE CURVES

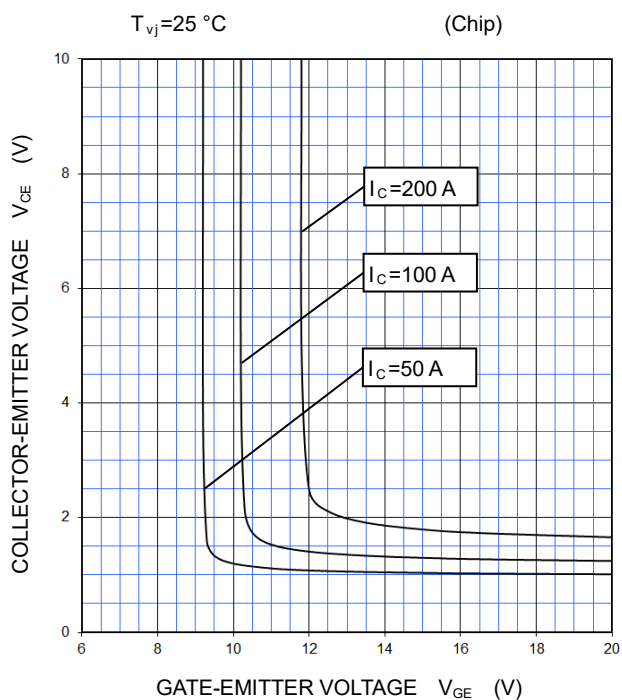
**OUTPUT CHARACTERISTICS
(TYPICAL)**



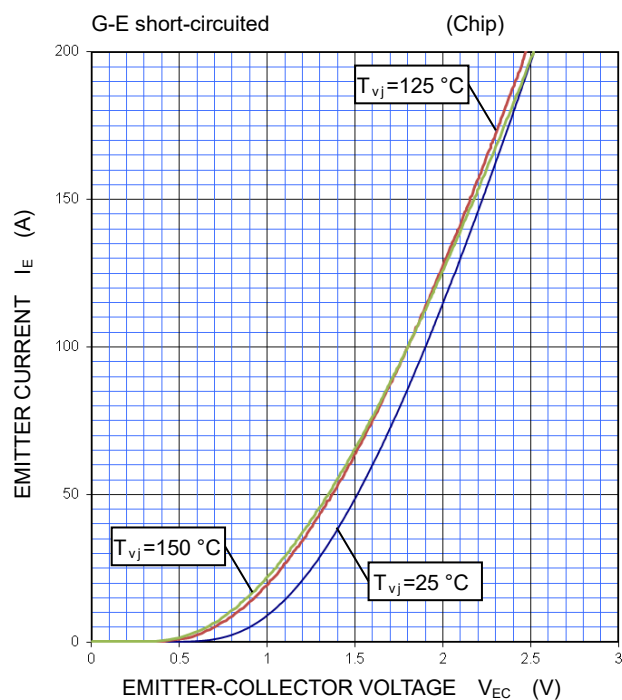
**COLLECTOR-EMITTER SATURATION VOLTAGE
CHARACTERISTICS
(TYPICAL)**



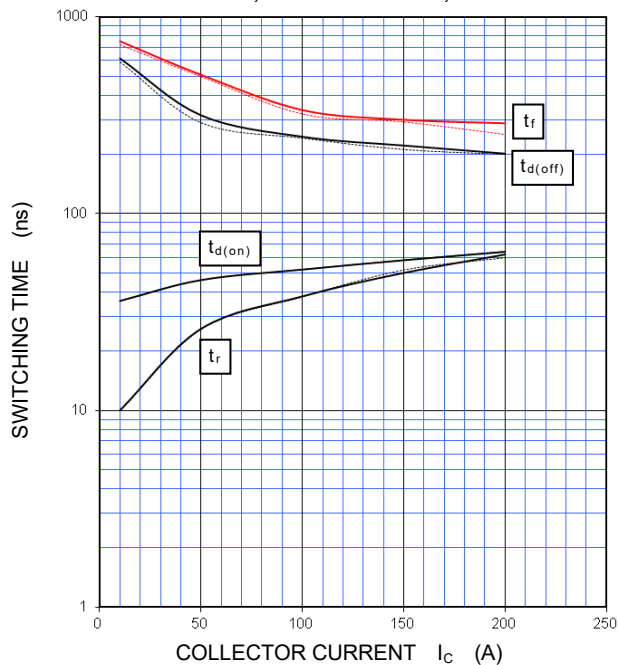
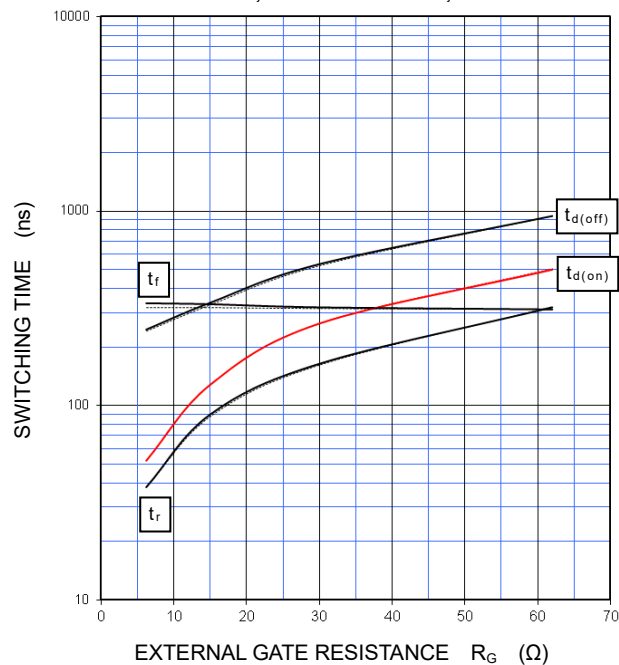
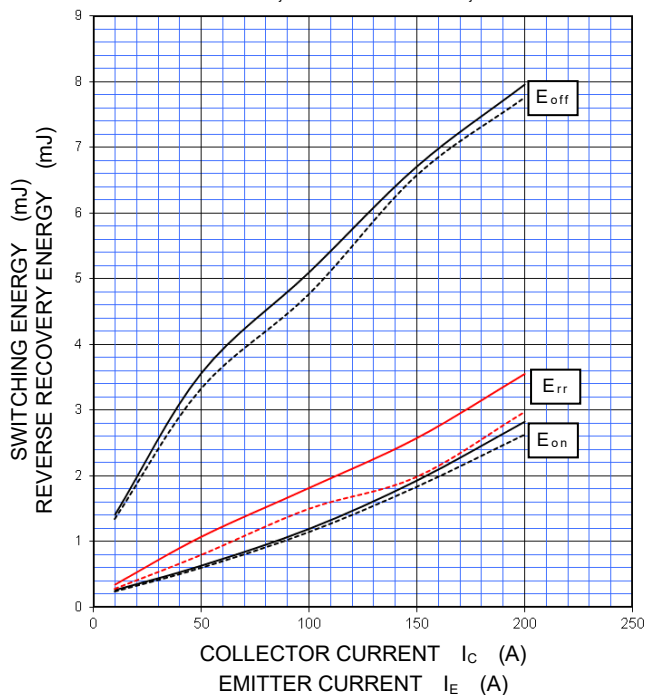
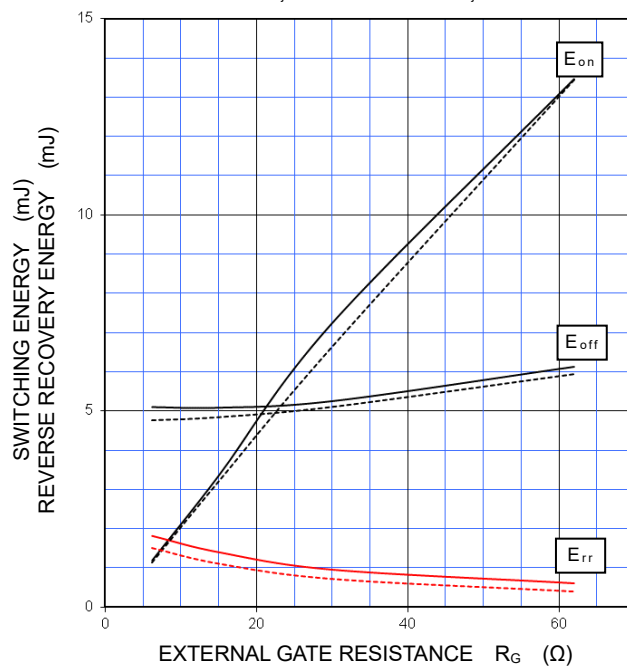
**COLLECTOR-EMITTER VOLTAGE CHARACTERISTICS
(TYPICAL)**



**FREE WHEELING DIODE
FORWARD CHARACTERISTICS
(TYPICAL)**

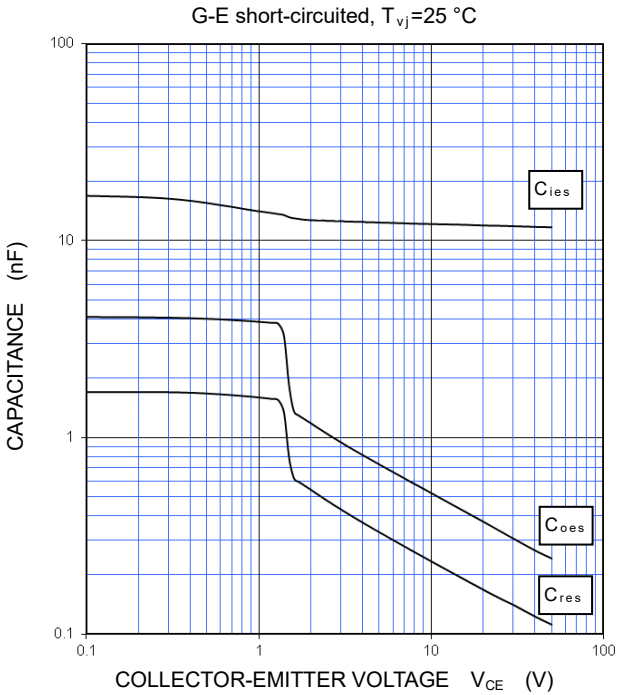


PERFORMANCE CURVES

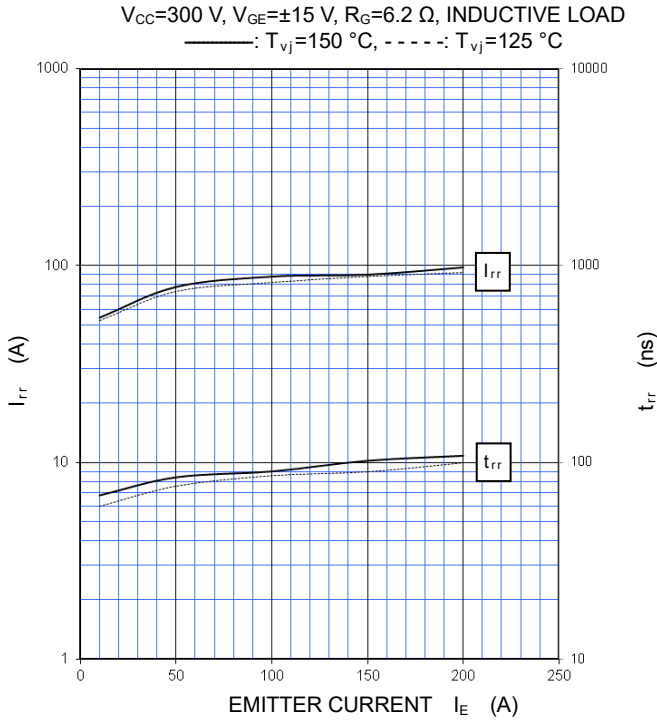
HALF-BRIDGE SWITCHING CHARACTERISTICS
(TYPICAL) $V_{CC}=300\text{ V}$, $V_{GE}=\pm 15\text{ V}$, $R_G=6.2\ \Omega$, INDUCTIVE LOAD
—: $T_{vj}=150\text{ }^\circ\text{C}$, - - - -: $T_{vj}=125\text{ }^\circ\text{C}$ HALF-BRIDGE SWITCHING CHARACTERISTICS
(TYPICAL) $V_{CC}=300\text{ V}$, $V_{GE}=\pm 15\text{ V}$, $I_C=100\text{ A}$, INDUCTIVE LOAD
—: $T_{vj}=150\text{ }^\circ\text{C}$, - - - -: $T_{vj}=125\text{ }^\circ\text{C}$ HALF-BRIDGE SWITCHING CHARACTERISTICS
(TYPICAL) $V_{CC}=300\text{ V}$, $V_{GE}=\pm 15\text{ V}$, $R_G=6.2\ \Omega$,
INDUCTIVE LOAD, PER PULSE
—: $T_{vj}=150\text{ }^\circ\text{C}$, - - - -: $T_{vj}=125\text{ }^\circ\text{C}$ HALF-BRIDGE SWITCHING CHARACTERISTICS
(TYPICAL) $V_{CC}=300\text{ V}$, $V_{GE}=\pm 15\text{ V}$, $I_C/I_E=100\text{ A}$,
INDUCTIVE LOAD, PER PULSE
—: $T_{vj}=150\text{ }^\circ\text{C}$, - - - -: $T_{vj}=125\text{ }^\circ\text{C}$ 

PERFORMANCE CURVES

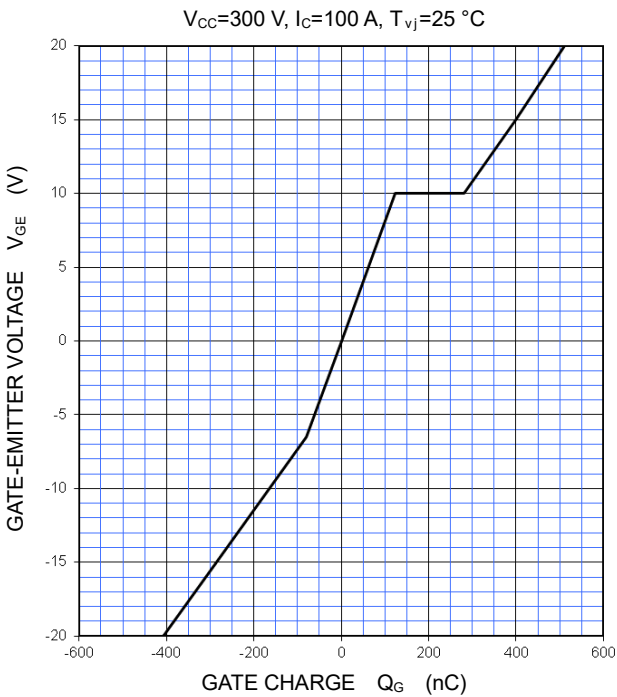
CAPACITANCE CHARACTERISTICS
(TYPICAL)



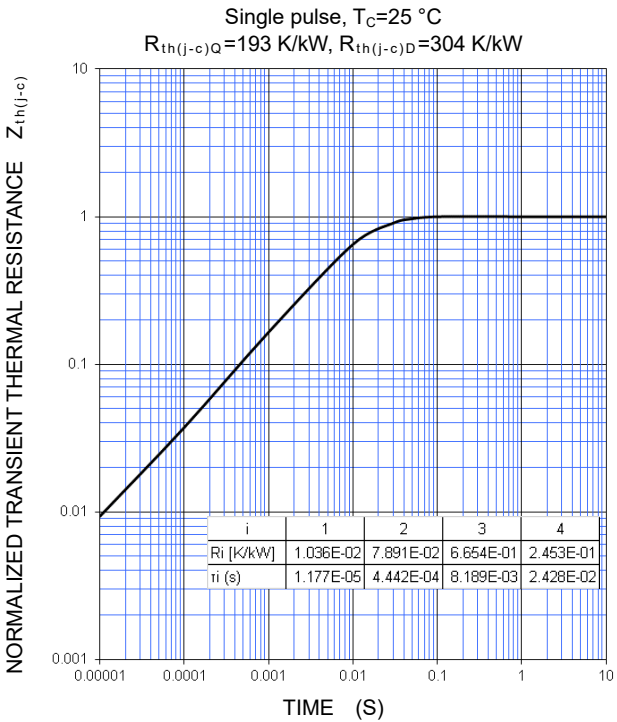
FREE WHEELING DIODE
REVERSE RECOVERY CHARACTERISTICS
(TYPICAL)



GATE CHARGE CHARACTERISTICS
(TYPICAL)

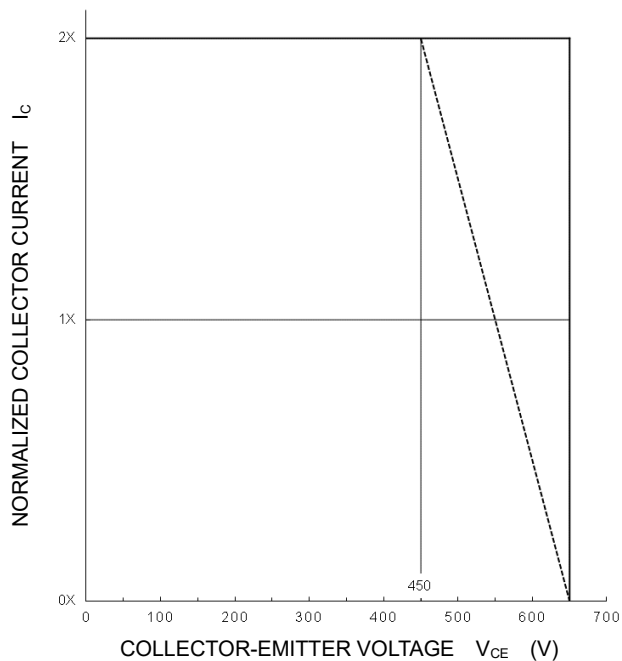


TRANSIENT THERMAL IMPEDANCE CHARACTERISTICS
(MAXIMUM)

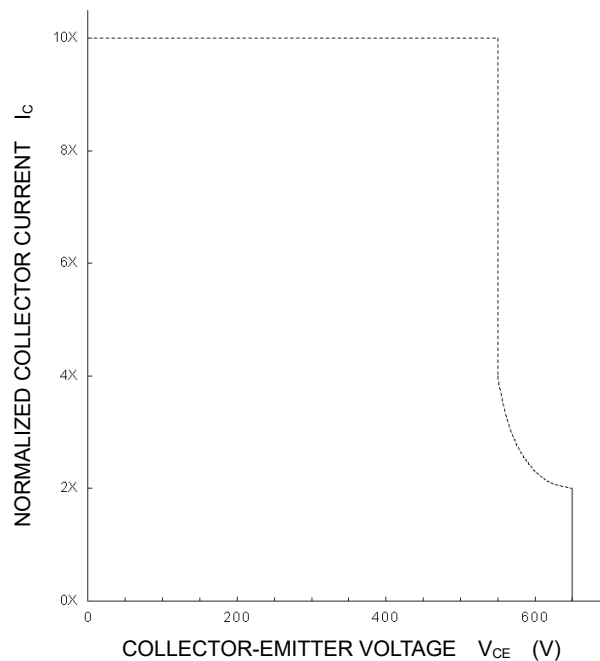


CM100DY-13THIGH POWER SWITCHING USE
INSULATED TYPE**PERFORMANCE CURVES****TURN-OFF SWITCHING SAFE OPERATING AREA
(REVERSE BIAS SAFE OPERATING AREA)
(MAXIMUM)**

$V_{CC} \leq 450 \text{ V}$, $V_{GE} = \pm 15 \text{ V}$, $R_G = 6.2 \sim 62 \Omega$,
 —: $T_{vj} = 25 \sim 150 \text{ }^\circ\text{C}$ (Normal load operations (Continuous))
 - - - - : $T_{vj} = 175 \text{ }^\circ\text{C}$ (Unusual load operations (Limited period))

**SHORT-CIRCUIT SAFE OPERATING AREA
(MAXIMUM)**

$V_{CC} \leq 400 \text{ V}$, $V_{GE} = \pm 15 \text{ V}$, $R_G = 6.2 \sim 62 \Omega$,
 $T_{vj} = 25 \sim 150 \text{ }^\circ\text{C}$, $t_W \leq 8 \mu\text{s}$, Non-Repetitive



Note: The characteristics curves are presented for reference only and not guaranteed by production test, unless otherwise noted.

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